

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

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Claim 1 (original): A method for transferring a device, comprising the steps of:  
  
irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;  
  
transferring the released device onto a device holding layer included on a device holding substrate; and  
  
transferring the device from the device holding layer onto a second substrate.

β' Claim 2 (original): A method for transferring a device as claimed in claim 1, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

Claim 3 (original): A method for transferring a device as claimed in claim 1, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 4 (original): A method for transferring a device as claimed in claim 1, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 5 (original): A method for transferring a device as claimed in claim 4, wherein the material is a nitride semiconductor material.

Claim 6 (original): A method for transferring a device as claimed in claim 5, wherein the nitride semiconductor material is a GaN-based material.

Claim 7 (original): A method for transferring a device as claimed in claim 1, wherein the first substrate is a sapphire substrate.

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Claim 8 (canceled)

Claim 9 (original): A method for transferring a device as claimed in claim 1, wherein the device is a light-emitting device.

Claim 10 (canceled)

Claim 11 (original): A method for transferring a device as claimed in claim 1, wherein the device holding layer is a silicone resin layer.

Claim 12 (original): A method for producing a device holding substrate, comprising the steps of:

preparing a substrate that includes a device having a pointed head portion;

providing an uncured silicone resin layer on a device holding substrate;

adhering the substrate that includes the device having the pointed head portion to the device holding substrate; and

providing a recessed portion in a surface of the silicone resin layer shaped to fit the pointed head portion.

Claim 13 (canceled)

Claim 14 (original): A device holding substrate, comprising:

a substrate; and

a silicone resin layer provided on the substrate, wherein a surface of the silicone resin layer has a recessed portion shaped to fit a pointed head portion of a device.

Claim 15 (previously added): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having one of a pointed head portion and a flat plate-shaped structure, included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate; and

transferring the device from the device holding layer onto a second substrate.

Claim 16 (previously added): A method for transferring a device as claimed in claim 15, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

Claim 17 (previously added): A method for transferring a device as claimed in claim 15, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

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Claim 18 (previously added): A method for transferring a device as claimed in claim 15, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 19 (previously added): A method for transferring a device as claimed in claim 18, wherein the material is a nitride semiconductor material.

Claim 20 (previously added): A method for transferring a device as claimed in claim 19, wherein the nitride semiconductor material is a GaN-based material.

Claim 21 (previously added): A method for transferring a device as claimed in claim 15, wherein the first substrate is a sapphire substrate.

Claim 22 (previously added): A method for transferring a device as claimed in claim 15, wherein the device is a light-emitting device.

Claim 23 (previously added): A method for transferring a device as claimed in claim 15, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

B' cont'd  
Claim 24 (previously added): A method for transferring a device as claimed in claim 15, wherein the device holding layer is a silicone resin layer.

Claim 25 (previously added): A method for producing a device holding substrate, comprising the steps of:

preparing a substrate that includes a device having a pointed head portion;

providing an uncured silicone resin layer on a device holding substrate;

coating the device having a pointed head portion with a release agent;

adhering the substrate that includes the device having the pointed head portion to the device holding substrate; and

providing a recessed portion in a surface of the silicone resin layer shaped to fit the pointed head portion.

Claim 26 (previously added): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device included on the first substrate with an energy beam to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

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Claim 27 (previously added): A method for transferring a device as claimed in claim 26, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 28 (previously added): A method for transferring a device as claimed in claim 26, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

Claim 29 (previously added): A method for transferring a device as claimed in claim 28, wherein the material is a nitride semiconductor material.

Claim 30 (previously added): A method for transferring a device as claimed in claim 29, wherein the nitride semiconductor material is a GaN-based material.

Claim 31 (previously added): A method for transferring a device as claimed in claim 26, wherein the first substrate is a sapphire substrate.

Claim 32 (canceled)

B' cont'd  
Claim 33 (previously added): A method for transferring a device as claimed in claim 26, wherein the device is a light-emitting device.

Claim 34 (previously added): A method for transferring a device as claimed in claim 26, wherein the device has a pointed head portion, and the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

Claim 35 (previously added): A method for transferring a device as claimed in claim 26, wherein the device holding layer is a silicone resin layer.

Claim 36 (new): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having a pointed head portion included on the first substrate with an energy beam and transmitting the energy beam through the first substrate to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion; and

transferring the device from the device holding layer onto a second substrate.

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Claim 37 (new): A method for transferring a device as claimed in claim 36, further comprising the step of cleaning the device on the device holding layer after the device is transferred onto the device holding layer.

Claim 38 (new): A method for transferring a device as claimed in claim 36, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 39 (new): A method for transferring a device as claimed in claim 36, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.



Claim 40 (new): A method for transferring a device as claimed in claim 39, wherein the material is a nitride semiconductor material.

Claim 41 (new): A method for transferring a device as claimed in claim 40, wherein the nitride semiconductor material is a GaN-based material.

Claim 42 (new): A method for transferring a device as claimed in claim 36, wherein the first substrate is a sapphire substrate.

Claim 43 (new): A method for transferring a device as claimed in claim 36, wherein the device is a light-emitting device.

Claim 44 (new): A method for transferring a device as claimed in claim 36, wherein the device holding layer is a silicone resin layer.

Claim 45 (new): A method for transferring a device, comprising the steps of:

irradiating, selectively, an interface between a first substrate and a device having a pointed head portion and a flat plate-shaped structure included on the first substrate with an energy beam to selectively release the device;

transferring the released device onto a device holding layer included on a device holding substrate;

cleaning the device on the device holding layer; and

transferring the device from the device holding layer onto a second substrate.

Claim 46 (new): A method for transferring a device as claimed in claim 45, further comprising the step of providing an adhesive layer on the second substrate wherein the adhesive layer is irradiated with the energy beam when the device is transferred from the device holding layer onto the second substrate.

Claim 47 (new): A method for transferring a device as claimed in claim 45, wherein the device is formed of a material which produces ablation upon irradiation with the energy beam, and wherein ablation is generated by the selective irradiation with the energy beam to cause exfoliation at an interface between the device and the first substrate.

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Claim 48 (new): A method for transferring a device as claimed in claim 47, wherein the material is a nitride semiconductor material.

Claim 49 (new): A method for transferring a device as claimed in claim 48, wherein the nitride semiconductor material is a GaN-based material.

Claim 50 (new): A method for transferring a device as claimed in claim 45, wherein the first substrate is a sapphire substrate.

Claim 51 (new): A method for transferring a device as claimed in claim 45, wherein the device is a light-emitting device.

Claim 52 (new): A method for transferring a device as claimed in claim 45, wherein the device holding layer includes a surface with a recessed portion shaped to fit the pointed head portion.

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Claim 53 (new): A method for transferring a device as claimed in claim 45, wherein the device holding layer is a silicone resin layer.

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